Details

Product Status	Obsolete
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, I²S, POR, PWM, WDT
Number of I/O	26
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	38-TFSOP (0.173", 4.40mm Width)
Supplier Device Package	PG-TSSOP-38-9
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc1201t038f0016aaxuma1

XMC1200

Microcontroller Series
for Industrial Applications

XMC1000 Family

ARM® Cortex™-M0
32-bit processor core

Data Sheet
V1.4 2014-05

Microcontrollers

Table 1   Synopsis of XMC1200 **Device Types** (cont'd)

Derivative	Package	Flash Kbytes	SRAM Kbytes
XMC1200-T038F0200	PG-TSSOP-38-9	200	16
XMC1202-T028X0016	PG-TSSOP-28-16	16	16
XMC1202-T028X0032	PG-TSSOP-28-16	32	16
XMC1202-T016X0016	PG-TSSOP-16-8	16	16
XMC1202-T016X0032	PG-TSSOP-16-8	32	16
XMC1202-Q024X0016	PG-VQFN-24-19	16	16
XMC1202-Q024X0032	PG-VQFN-24-19	32	16
XMC1201-Q040F0016	PG-VQFN-40-13	16	16
XMC1201-Q040F0032	PG-VQFN-40-13	32	16
XMC1201-Q040F0064	PG-VQFN-40-13	64	16
XMC1201-Q040F0128	PG-VQFN-40-13	128	16
XMC1201-Q040F0200	PG-VQFN-40-13	200	16
XMC1202-Q040X0016	PG-VQFN-40-13	16	16
XMC1202-Q040X0032	PG-VQFN-40-13	32	16

1.3   Device Type Features

The following table lists the available features per device type.

Table 2   Features of XMC1200 Device Types[1]

Derivative	ADC channel	ACMP	BCCU	LEDTS
XMC1200-T038	16	3	1	2
XMC1201-T038	16	-	-	2
XMC1202-T028	14	3	1	-
XMC1202-T016	11	2	1	-
XMC1202-Q024	13	3	1	-
XMC1201-Q040	16	-	-	2
XMC1202-Q040	16	3	1	-

1) Features that are not included in this table are available in all the derivatives
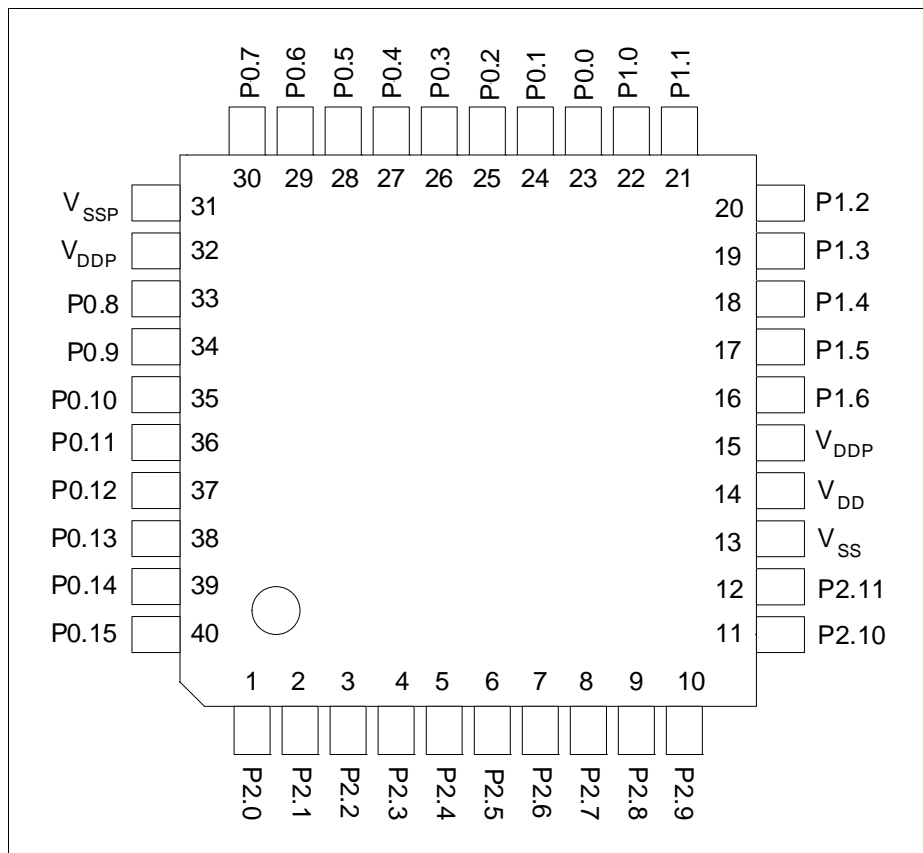
Figure 8 **XMC1200 PG-VQFN-40 Pin Configuration** (top view)

Table 6   Package Pin Mapping

Function	VQFN 40	TSSOP 38	TSSOP 28	VQFN 24	TSSOP 16	Pad Type	Notes
P0.13	38	32	22	22	-	STD_INOUT	
P0.14	39	33	23	23	13	STD_INOUT	
P0.15	40	34	24	24	14	STD_INOUT	
P1.0	22	16	12	14	-	High Current	
P1.1	21	15	11	13	-	High Current	
P1.2	20	14	10	12	-	High Current	
P1.3	19	13	9	11	-	High Current	
P1.4	18	12	-	-	-	High Current	
P1.5	17	11	-	-	-	High Current	
P1.6	16	-	-	-	-	STD_INOUT	
P2.0	1	35	25	1	15	STD_INOUT /AN	
P2.1	2	36	26	2	-	STD_INOUT /AN	
P2.2	3	37	27	3	-	STD_IN/AN	
P2.3	4	38	-	-	-	STD_IN/AN	
P2.4	5	1	-	-	-	STD_IN/AN	
P2.5	6	2	28	-	-	STD_IN/AN	
P2.6	7	3	1	4	16	STD_IN/AN	
P2.7	8	4	2	5	1	STD_IN/AN	
P2.8	9	5	3	5	1	STD_IN/AN	
P2.9	10	6	4	6	2	STD_IN/AN	
P2.10	11	7	5	7	3	STD_INOUT /AN	
P2.11	12	8	6	8	4	STD_INOUT /AN	
VSS	13	9	7	9	5	Power	Supply GND, ADC reference GND

Table 6   Package Pin Mapping

Function	VQFN 40	TSSOP 38	TSSOP 28	VQFN 24	TSSOP 16	Pad Type	Notes
VDD	14	10	8	10	6	Power	Supply VDD, ADC reference voltage/ORC reference voltage. VDD has to be supplied with the same voltage as VDDP
VDDP	15	10	8	10	6	Power	I/O port supply
VSSP	31	25	-	-	-	Power	I/O port ground
VDDP	32	26	-	-	-	Power	I/O port supply
VSSP	Exp. Pad	-	-	Exp. Pad	-	Power	**Exposed Die Pad** The exposed die pad is connected internally to VSSP. For proper operation, it is mandatory to connect the exposed pad to the board ground. For thermal aspects, please refer to the Package and Reliability chapter.

3.2 DC Parameters

3.2.1 Input/Output Characteristics

Table 11 provides the characteristics of the input/output pins of the XMC1200.

Table 11   Input/Output Characteristics (Operating Conditions apply)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Output low voltage on port pins (with standard pads)	V_{OLP}	CC	–	1.0	V	I_{OL} = 11 mA (5 V) I_{OL} = 7 mA (3.3 V)
			–	0.4	V	I_{OL} = 5 mA (5 V) I_{OL} = 3.5 mA (3.3 V)
Output low voltage on high current pads	V_{OLP1}	CC	–	1.0	V	I_{OL} = 50 mA (5 V) I_{OL} = 25 mA (3.3 V)
			–	0.32	V	I_{OL} = 10 mA (5 V)
			–	0.4	V	I_{OL} = 5 mA (3.3 V)
Output high voltage on port pins (with standard pads)	V_{OHP}	CC	V_{DDP} - 1.0	–	V	I_{OH} = -10 mA (5 V) I_{OH} = -7 mA (3.3 V)
			V_{DDP} - 0.4	–	V	I_{OH} = -4.5 mA (5 V) I_{OH} = -2.5 mA (3.3 V)
Output high voltage on high current pads	V_{OHP1}	CC	V_{DDP} - 0.32	–	V	I_{OH} = -6 mA (5 V)
			V_{DDP} - 1.0	–	V	I_{OH} = -8 mA (3.3 V)
			V_{DDP} - 0.4	–	V	I_{OH} = -4 mA (3.3 V)
Input low voltage on port pins (Standard Hysteresis)	V_{ILPS}	SR	–	$0.19 \times V_{DDP}$	V	CMOS Mode (5 V, 3.3 V & 2.2 V)
Input high voltage on port pins (Standard Hysteresis)	V_{IHPS}	SR	$0.7 \times V_{DDP}$	–	V	CMOS Mode (5 V, 3.3 V & 2.2 V)
Input low voltage on port pins (Large Hysteresis)	V_{ILPL}	SR	–	$0.08 \times V_{DDP}$	V	CMOS Mode (5 V, 3.3 V & 2.2 V)[3]

Table 11 **Input/Output Characteristics (Operating Conditions apply)** (cont'd)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Maximum current into V_{DDP} (TSSOP28/16, VQFN24)	I_{MVDD1}	SR	–	130	mA	3)
Maximum current into V_{DDP} (TSSOP38, VQFN40)	I_{MVDD2}	SR	–	260	mA	3)
Maximum current out of V_{SS} (TSSOP28/16, VQFN24)	I_{MVSS1}	SR	–	130	mA	3)
Maximum current out of V_{SS} (TSSOP38, VQFN40)	I_{MVSS2}	SR	–	260	mA	3)

1) Not subject to production test, verified by design/characterization. Hysteresis is implemented to avoid meta stable states and switching due to internal ground bounce. It cannot be guaranteed that it suppresses switching due to external system noise.

2) An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin.

3) Not subject to production test, verified by design/characterization.

4) Not subject to production test, verified by design/characterization. However, for applications with strict low power-down current requirements, it is mandatory that no active voltage source is supplied at any GPIO pin when V_{DDP} is powered off.

Table 12   ADC Characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gain settings	G_{IN} CC		1		–	GNCTRxz.GAINy = 00_B (unity gain)
			3		–	GNCTRxz.GAINy = 01_B (gain g1)
			6		–	GNCTRxz.GAINy = 10_B (gain g2)
			12		–	GNCTRxz.GAINy = 11_B (gain g3)
Sample Time	t_{sample} CC	3	–	–	1 / f_{ADC}	V_{DDP} = 5.0 V
		3	–	–	1 / f_{ADC}	V_{DDP} = 3.3 V
		30	–	–	1 / f_{ADC}	V_{DDP} = 1.8 V
Sigma delta loop hold time	t_{SD_hold} CC	20	–	–	µs	Residual charge stored in an active sigma delta loop remains available
Conversion time in fast compare mode	t_{CF} CC		9		1 / f_{ADC}	[2]
Conversion time in 12-bit mode	t_{C12} CC		20		1 / f_{ADC}	[2]
Maximum sample rate in 12-bit mode [3]	f_{C12} CC	–	–	f_{ADC} / 42.5	–	1 sample pending
		–	–	f_{ADC} / 62.5	–	2 samples pending
Conversion time in 10-bit mode	t_{C10} CC		18		1 / f_{ADC}	[2]
Maximum sample rate in 10-bit mode [3]	f_{C10} CC	–	–	f_{ADC} / 40.5	–	1 sample pending
		–	–	f_{ADC} / 58.5	–	2 samples pending
Conversion time in 8-bit mode	t_{C8} CC		16		1 / f_{ADC}	[2]

3.2.3 Out of Range Comparator (ORC) Characteristics

The Out-of-Range Comparator (ORC) triggers on analog input voltages (V_{AIN}) above the V_{DDP} on selected input pins (ORCx.AIN) and generates a service request trigger (ORCx.OUT).

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 13   Out of Range Comparator (ORC) Characteristics (Operating Conditions apply; V_{DDP} = 3.0 V - 5.5 V)

| Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
DC Switching Level	V_{ODC}	CC	60	–	120	mV	$V_{AIN} \geq V_{DDP} + V_{ODC}$
Hysteresis	V_{OHYS}	CC	25	–	V_{ODC}	mV	
Always detected Overvoltage Pulse	t_{OPDD}	CC	103	–	–	ns	$V_{AIN} \geq V_{DDP}$ + 150 mV
			88	–	–	ns	$V_{AIN} \geq V_{DDP}$ + 350 mV
Never detected Overvoltage Pulse	t_{OPDN}	CC	–	–	21	ns	$V_{AIN} \geq V_{DDP}$ + 150 mV
			–	–	11	ns	$V_{AIN} \geq V_{DDP}$ + 350 mV
Detection Delay	t_{ODD}	CC	39	–	132	ns	$V_{AIN} \geq V_{DDP}$ + 150 mV
			31	–	121	ns	$V_{AIN} \geq V_{DDP}$ + 350 mV
Release Delay	t_{ORD}	CC	44	–	240	ns	$V_{AIN} \leq V_{DDP}$; V_{DDP} = 5 V
			57	–	340	ns	$V_{AIN} \leq V_{DDP}$; V_{DDP} = 3.3 V
Enable Delay	t_{OED}	CC	–	–	300	ns	ORCCTRL.ENORCx = 1
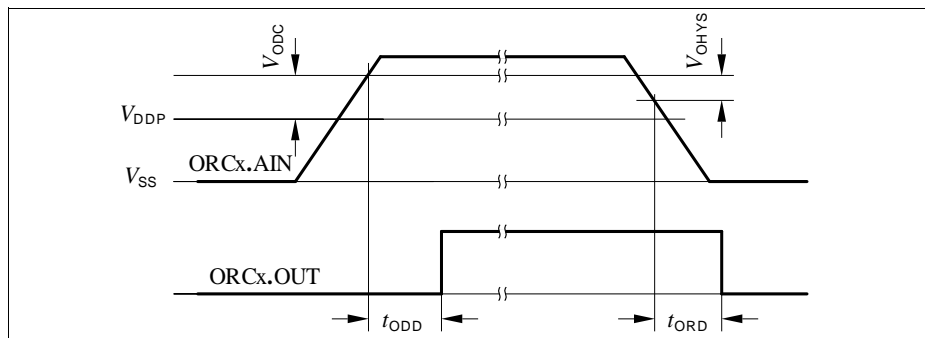
Figure 10   ORCx.OUT Trigger Generation

3.2.6 Power Supply Current

The total power supply current defined below consists of a leakage and a switching component.

Application relevant values are typically lower than those given in the following tables, and depend on the customer's system operating conditions (e.g. thermal connection or used application configurations).

Table 16 Power Supply Parameters[1]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.[2]	Max.		
Active mode current[3]	I_{DDPA} CC	–	8.8	11.5	mA	f_{MCLK} = 32 MHz f_{PCLK} = 64 MHz
		–	3.9	–	mA	f_{MCLK} = 1 MHz f_{PCLK} = 1 MHz
Sleep mode current Peripherals clock enabled[4]	I_{DDPSE} CC	–	6.2	–	mA	f_{MCLK} = 32 MHz f_{PCLK} = 64 MHz
Sleep mode current Peripherals clock disabled[5]	I_{DDPSD} CC	–	1.2	–	mA	f_{MCLK} = 1 MHz f_{PCLK} = 1 MHz
Deep Sleep mode current[6]	I_{DDPDS} CC	–	0.24	–	mA	
Wake-up time from Sleep to Active mode[7]	t_{SSA} CC	–	6	–	cycles	
Wake-up time from Deep Sleep to Active mode[8]	t_{DSA} CC	–	280	–	μsec	

1) Not all parameters are 100% tested, but are verified by design/characterisation and test correlation.

2) The typical values are measured at T_A = + 25 °C and V_{DDP} = 5 V.

3) CPU and all peripherals clock enabled, Flash is in active mode.

4) CPU is sleep, all peripherals clock enabled and Flash is in active mode.

5) CPU is sleep, Flash is powered down and code executed from RAM after wake-up.

6) CPU is sleep, peripherals clock disabled, Flash is powered down and code executed from RAM after wake-up.

7) CPU is sleep, Flash is in active mode during sleep mode.

8) CPU is sleep, Flash is in power down mode during deep sleep mode.

3.2.7 Flash Memory Parameters

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 18   Flash Memory Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	**Typ.**	**Max.**		
Erase Time per page	t_{ERASE} CC	6.8	7.1	7.6	ms	
Program time per block	t_{PSER} CC	102	152	204	µs	
Wake-Up time	t_{WU} CC	–	32.2	–	µs	
Read time per word	t_a CC	–	50	–	ns	
Data Retention Time	t_{RET} CC	10	–	–	years	Max. 100 erase / program cycles
Flash Wait States [1]	$N_{WSFLASH}$ CC	0	0.5	–		f_{MCLK} = 8 MHz
		0	1.4	–		f_{MCLK} = 16 MHz
		1	1.9	–		f_{MCLK} = 32 MHz
Erase Cycles per page	N_{ECYC} CC	–	–	$5*10^4$	cycles	
Total Erase Cycles	N_{TECYC} CC	–	–	$2*10^6$	cycles	

1) Flash wait states are automatically inserted by the Flash module during memory read when needed. Typical values are calculated from the execution of the Dhrystone benchmark program.

3.3.3 Power-Up and Supply Threshold Charcteristics

Table 20 provides the characteristics of the supply threshold in XMC1200.

Table 20 **Power-Up and Supply Threshold Parameters (Operating Conditions apply)** [1]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	**Typ.**	**Max.**		
V_{DDP} ramp-up time	t_{RAMPUP} SR	$V_{DDP}/S_{VDDPrise}$	–	10^7	µs	
V_{DDP} slew rate	S_{VDDPOP} SR	0	–	0.1	V/µs	Slope during normal operation
	S_{VDDP10} SR	0	–	10	V/µs	Slope during fast transient within +/- 10% of V_{DDP}
	$S_{VDDPrise}$ SR	0	–	10	V/µs	Slope during power-on or restart after brownout event
	$S_{VDDPfall}$ [2] SR	0	–	0.25	V/µs	Slope during supply falling out of the +/-10% limits[3]
V_{DDP} prewarning voltage	V_{DDPPW} CC	2.1	2.25	2.4	V	ANAVDEL.VDEL_SELECT = 00$_B$
		2.85	3	3.15	V	ANAVDEL.VDEL_SELECT = 01$_B$
		4.2	4.4	4.6	V	ANAVDEL.VDEL_SELECT = 10$_B$
V_{DDP} brownout reset voltage	V_{DDPBO} CC	1.55	1.62	1.75	V	calibrated, before user code starts running
Start-up time from power-on reset	t_{SSW} SR	–	320	–	µs	Time to the first user code instruction[4]

1) Not all parameters are 100% tested, but are verified by design/characterisation.

2) A capacitor of at least 100 nF has to be added between V_{DDP} and V_{SSP} to fulfill the requirement as stated for this parameter.

3.3.4 On-Chip Oscillator Characteristics

Table 21 provides the characteristics of the 64 MHz clock output from the digital controlled oscillator, DCO1 in XMC1200.

Table 21   64 MHz DCO1 Characteristics (Operating Conditions apply)

Parameter	Symbol		Limit Values			Unit	Test Conditions
			Min.	Typ.	Max.		
Nominal frequency	f_{NOM}	CC	63.5	64	64.5	MHz	under nominal conditions[1] after trimming
Accuracy	Δf_{LT}	CC	-1.7	–	3.4	%	with respect to f_{NOM}(typ), over temperature (0 °C to 85 °C)[2]
			-3.9	–	4.0	%	with respect to f_{NOM}(typ), over temperature (-40 °C to 105 °C)[2]
Accuracy with calibration based on temperature sensor	Δf_{LTT}	CC	-1.3	–	1.25	%	with respect to f_{NOM}(typ), over temperature (T_A = 0 °C to 105 °C)[2]
			-2.6	–	1.25	%	with respect to f_{NOM}(typ), over temperature (T_A = -40 °C to 105 °C)[2]

1) The deviation is relative to the factory trimmed frequency at nominal V_{DDC} and T_A = + 25 °C.

2) Not subject to production test, verified by design/characterisation.

3.3.7 Peripheral Timings

Note: These parameters are not subject to production test, but verified by design and/or characterization.

3.3.7.1 Synchronous Serial Interface (USIC SSC) Timing

The following parameters are applicable for a USIC channel operated in SSC mode.

Note: Operating Conditions apply.

Table 25 USIC SSC Master Mode Timing

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Slave select output SELO active to first SCLKOUT transmit edge	t_1	CC	80	–	–	ns	
Slave select output SELO inactive after last SCLKOUT receive edge	t_2	CC	0	–	–	ns	
Data output DOUT[3:0] valid time	t_3	CC	-10	–	10	ns	
Receive data input DX0/DX[5:3] setup time to SCLKOUT receive edge	t_4	SR	80	–	–	ns	
Data input DX0/DX[5:3] hold time from SCLKOUT receive edge	t_5	SR	0	–	–	ns	

Table 26 USIC SSC Slave Mode Timing

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Select input DX2 setup to first clock input DX1 transmit edge[1]	t_{10}	SR	10	–	–	ns	
Select input DX2 hold after last clock input DX1 receive edge[1]	t_{11}	SR	10	–	–	ns	

Table 26   USIC SSC Slave Mode Timing (cont'd)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Receive data input DX0/DX[5:3] setup time to shift clock receive edge[1]	t_{12}	SR	10	–	–	ns	
Data input DX0/DX[5:3] hold time from clock input DX1 receive edge[1]	t_{13}	SR	10	–	–	ns	
Data output DOUT[3:0] valid time	t_{14}	CC	-	–	80	ns	

1) These input timings are valid for asynchronous input signal handling of slave select input, shift clock input, and receive data input (bits DXnCR.DSEN = 0).
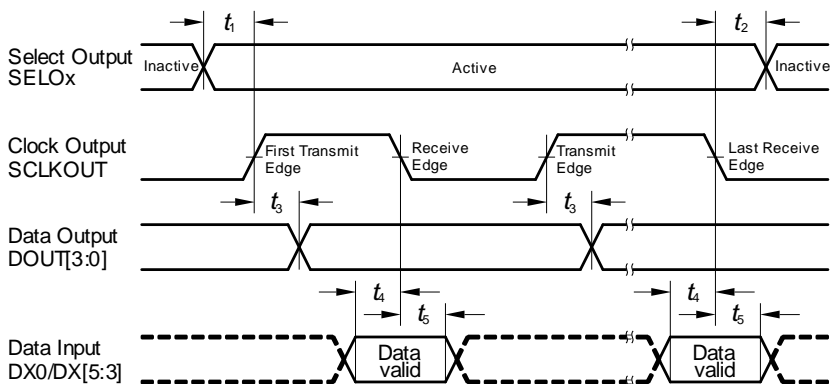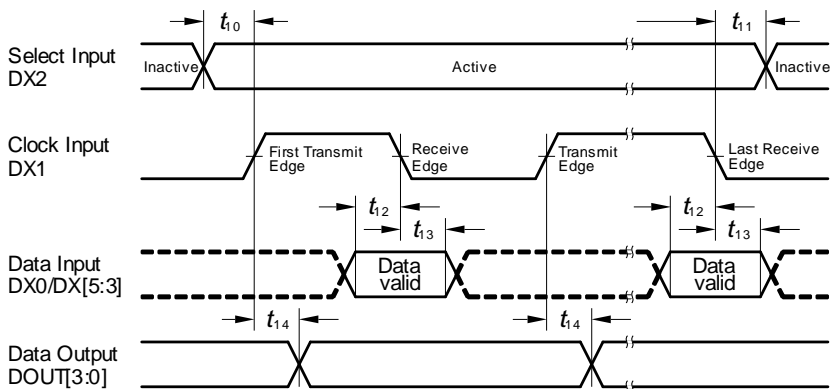
Figure 17   USIC - SSC Master/Slave Mode Timing

Note: This timing diagram shows a standard configuration, for which the slave select signal is low-active, and the serial clock signal is not shifted and not inverted.

The difference between junction temperature and ambient temperature is determined by

$\Delta T = (P_{INT} + P_{IOSTAT} + P_{IODYN}) \times R_{\Theta JA}$

The internal power consumption is defined as

$P_{INT} = V_{DDP} \times I_{DDP}$ (switching current and leakage current).

The static external power consumption caused by the output drivers is defined as

$P_{IOSTAT} = \Sigma((V_{DDP}-V_{OH}) \times I_{OH}) + \Sigma(V_{OL} \times I_{OL})$

The dynamic external power consumption caused by the output drivers (P_{IODYN}) depends on the capacitive load connected to the respective pins and their switching frequencies.

If the total power dissipation for a given system configuration exceeds the defined limit, countermeasures must be taken to ensure proper system operation:

- Reduce V_{DDP}, if possible in the system
- Reduce the system frequency
- Reduce the number of output pins
- Reduce the load on active output drivers

Figure 23   PG-TSSOP-16-8

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Figure 25   PG-VQFN-40-13

All dimensions in mm.

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